

AD1900-9 TO5i

Avalanche Photodiode, NIR enhanced

Special characteristics:

quantum efficiency >80% at λ 760-910 nm
high speed, low noise
1950 μm diameter active area
low slope multiplication curve



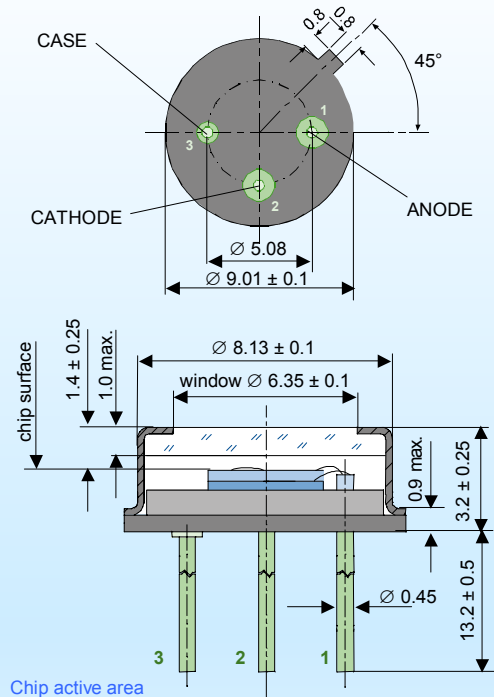
Parameters:	AD1900-9 TO5i
Active Area	3.0 mm ² Ø 1950 μm
Dark Current ¹⁾ (M = 100)	typ. 15.0 nA
Total Capacitance ¹⁾ (M = 100)	typ. 8 pF
Breakdown Voltage U _{BR} (at I _D = 2 μA)	120 ... 300 V typ. > 200 V
Temperature Coefficient of U _{BR}	typ. 1.55 V/K
Spectral Responsivity ¹⁾ (at 905 nm, M = 100)	min. 55 A/W typ. 60 A/W
Cut-off Frequency (-3dB)	typ. 0.25 GHz
Rise Time at 905 nm, 50 Ω	typ. 1.4 ns
Optimum Gain	50 - 60
Max. Gain	> 200
"Excess Noise" factor (M = 100)	typ. 2.5
"Excess Noise" index (M = 100)	typ. 0.2
N.E.P. (M = 100, 905 nm)	typ. 1.5* 10 ⁻¹³ W/Hz ^{1/2}
Operating Temperature	-20 ... +70°C
Storage Temperature	-60 ... +100°C

1) measurement conditions:

Setup of photo current 10 nA at M = 1 and irradiation by a IRED
(880 nm, 80 nm bandwidth).

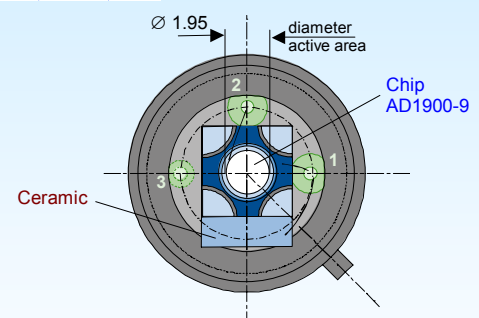
Increase the photo current up to 1 μA , (M = 100) by internal multiplication
due to an increasing bias voltage.

Package 3a (TO5i):

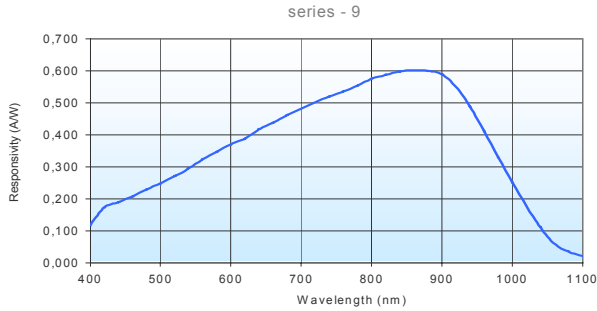


Chip active area

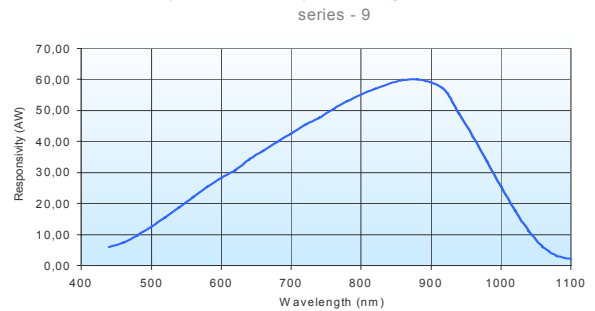
type	diameter	area
AD1900	1950	3.00
AD2500	2520	5.00



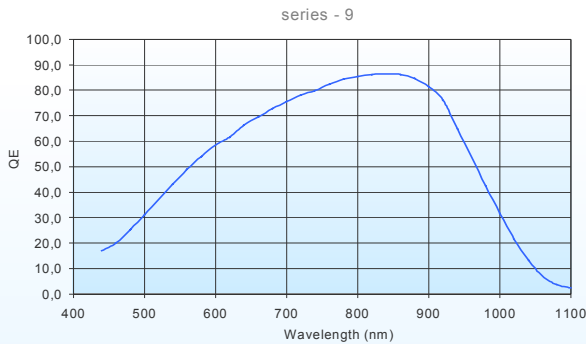
Spectral Responsivity at M=1



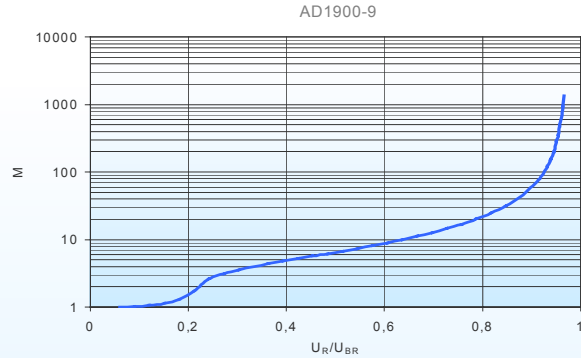
Spectral Responsivity at M=100



QE for M=100



Gain = $f(U_R/U_{BR})$ at $\lambda=880$ nm



Maximum Ratings:

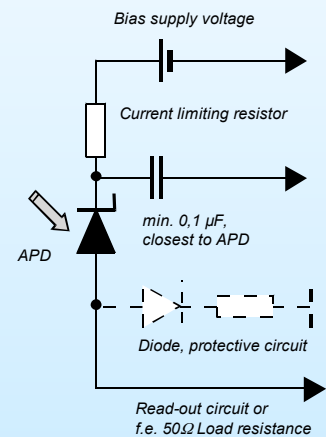
- max. electrical power dissipation 100 mW at 22°C
- max. optical peak value, once 200 mW for 1 s
- max. continuous optical operation $I_{Ph} (DC) \leq 250 \mu A$
- $(P_{electr.} = P_{opt.} * S_{abs} * M * U_R)$ ≤ 1 mA for signal 50 μs "on" / 1 ms "off"

Application Hints:

- Current should be limited by a protecting resistor or current limiting - IC inside the power supply.
- Use of low noise read-out - IC.
- For high gain applications bias voltage should be temperature compensated.
- For low light level applications, blocking of ambient light should be used.

Handling Precautions:

- Soldering temperature 260 °C for max. 10 s. The device must be protected against solder flux vapour!
- min. Pin - length 2 mm
- ESD - protection Standard precautionary measures are sufficient.
- Storage Store devices in conductive foam.
- Avoid skin contact with window!
- Clean window with Ethyl alcohol if necessary.
- Do not scratch or abrade window.



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